

N - CHANNEL ENHANCEMENT MODE

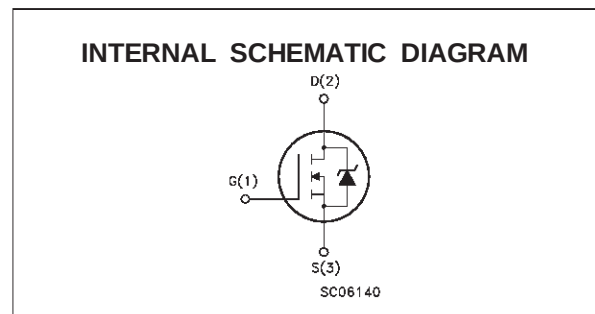
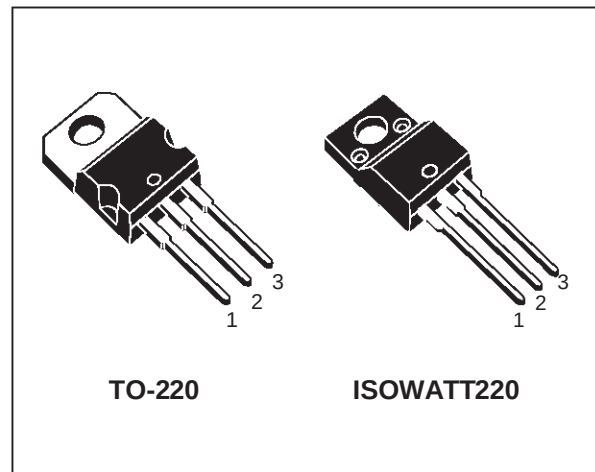
POWER MOS TRANSISTOR

TYPE	V _{DSS}	R _{DS(on)}	I _D
STP45N10	100 V	< 0.035 Ω	45 A
STP45N10FI	100 V	< 0.035 Ω	24 A

- TYPICAL R_{DS(on)} = 0.027 Ω
- AVALANCHE RUGGED TECHNOLOGY
- 100% AVALANCHE TESTED
- REPETITIVE AVALANCHE DATA AT 100°C
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- 175 °C OPERATING TEMPERATURE
- APPLICATION ORIENTED CHARACTERIZATION

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- DC-DC & DC-AC CONVERTERS
- AUTOMOTIVE ENVIRONMENT (INJECTION, ABS, AIR-BAG, LAMP DRIVERS. Etc.)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value		Unit
		STP45N10	STP45N10FI	
V _{DS}	Drain-source Voltage (V _{GS} = 0)	100		V
V _{DGR}	Drain- gate Voltage (R _{GS} = 20 k Ω)	100		V
V _{GS}	Gate-source Voltage	± 20		V
I _D	Drain Current (continuous) at T _c = 25 °C	45	24	A
I _D	Drain Current (continuous) at T _c = 100 °C	32	17	A
I _{DM} (•)	Drain Current (pulsed)	180	180	A
P _{tot}	Total Dissipation at T _c = 25 °C	150	45	W
	Derating Factor	1	0.3	W/°C
V _{ISO}	Insulation Withstand Voltage (DC)	—	2000	V
T _{stg}	Storage Temperature	-65 to 175		°C
T _j	Max. Operating Junction Temperature	175		°C

THERMAL DATA

				TO220	ISOWATT220	
R _{thj-case}	Thermal Resistance Junction-case	Max		1	3.33	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	Max		62.5		°C/W
R _{thc-sink}	Thermal Resistance Case-sink	Typ		0.5		°C/W
T _l	Maximum Lead Temperature For Soldering Purpose			300		°C

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I _{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T _j max, δ < 1%)	45	A
E _{AS}	Single Pulse Avalanche Energy (starting T _j = 25 °C, I _D = I _{AR} , V _{DD} = 25 V)	400	mJ

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA V _{GS} = 0	100			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating x 0.8 V _{DS} = Max Rating x 0.8 T _c = 125 °C			10 1 50	μA μA
I _{GSS}	Gate-Source Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			± 100	mA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2	3	4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 22.5 A V _{GS} = 10 V I _D = 22.5 A T _c = 100°C		0.027	0.035 0.07	Ω Ω
I _{D(on)}	On State Drain Current	V _{DS} > I _{D(on)} x R _{DS(on)max} V _{GS} = 10 V	45			A

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} > I _{D(on)} x R _{DS(on)max} I _D = 22.5 A	20	40		S
C _{iss}	Input Capacitance	V _{DS} = 25 V f = 1 MHz V _{GS} = 0		4100	5200	pF
C _{oss}	Output Capacitance			600	800	pF
C _{rss}	Reverse Transfer Capacitance			150	220	pF

ELECTRICAL CHARACTERISTICS (continued)**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on Time	$V_{DD} = 50\text{ V}$ $I_D = 22.5\text{ A}$		25	35	ns
t_r	Rise Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		75	105	ns
$(di/dt)_{on}$	Turn-on Current Slope	$V_{DD} = 80\text{ V}$ $I_D = 45\text{ A}$ $R_G = 47\ \Omega$ $V_{GS} = 10\text{ V}$		400		A/ μs
Q_g	Total Gate Charge	$V_{DD} = 80\text{ V}$ $I_D = 45\text{ A}$ $V_{GS} = 10\text{ V}$		120	170	nC
Q_{gs}	Gate-Source Charge			20		nC
Q_{gd}	Gate-Drain Charge			50		nC

SWITCHING OFF

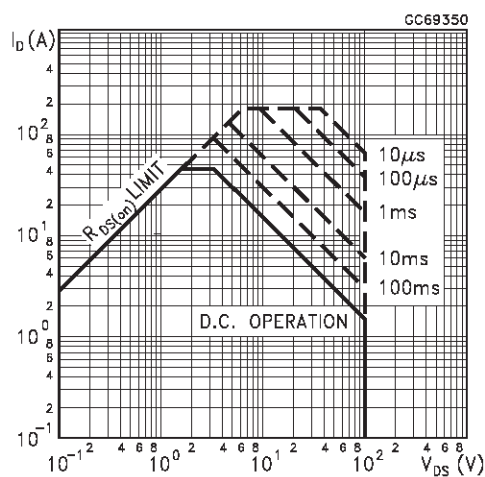
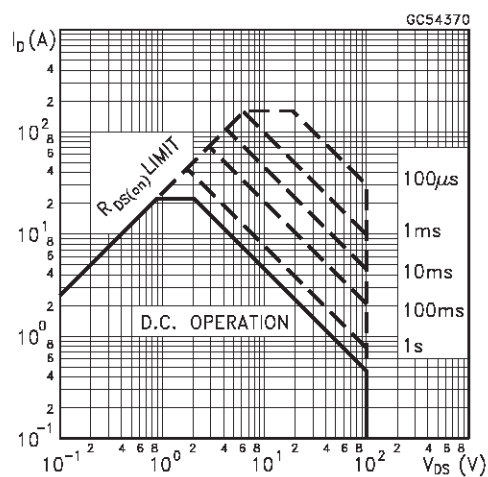
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(voff)}$	Off-voltage Rise Time	$V_{DD} = 80\text{ V}$ $I_D = 45\text{ A}$		30	45	ns
t_f	Fall Time	$R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		35	50	ns
t_c	Cross-over Time			65	95	ns

SOURCE DRAIN DIODE

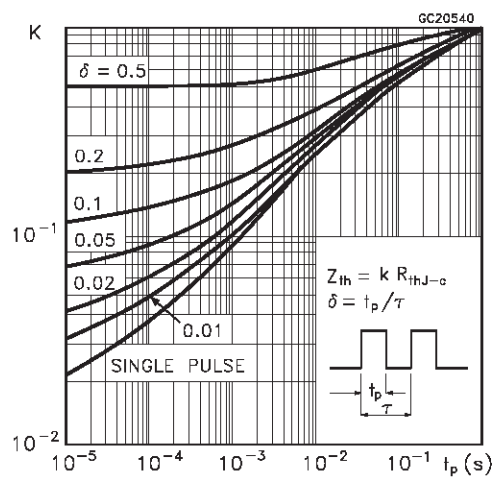
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain Current				45	A
$I_{SDM}(\bullet)$	Source-drain Current (pulsed)				180	A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 45\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr}	Reverse Recovery Time	$I_{SD} = 45\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 30\text{ V}$ $T_J = 150\text{ }^\circ\text{C}$		200		ns
Q_{rr}	Reverse Recovery Charge			0.14		μC
I_{RRM}	Reverse Recovery Current			14		A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

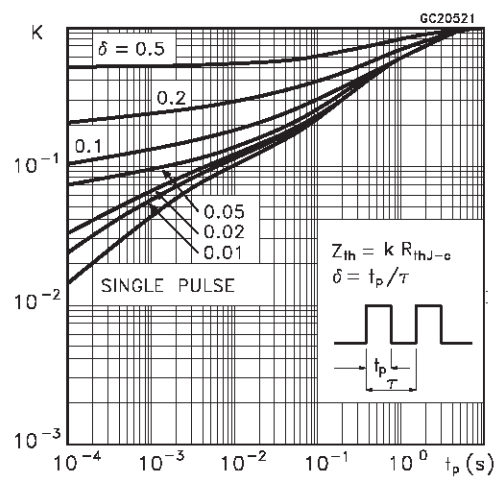
(\bullet) Pulse width limited by safe operating area

Safe Operating Area for TO-220**Safe Operating Area for ISOWATT220**

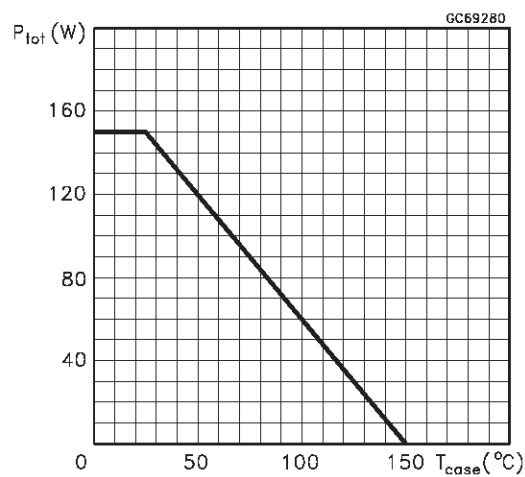
Thermal Impedance for TO-220



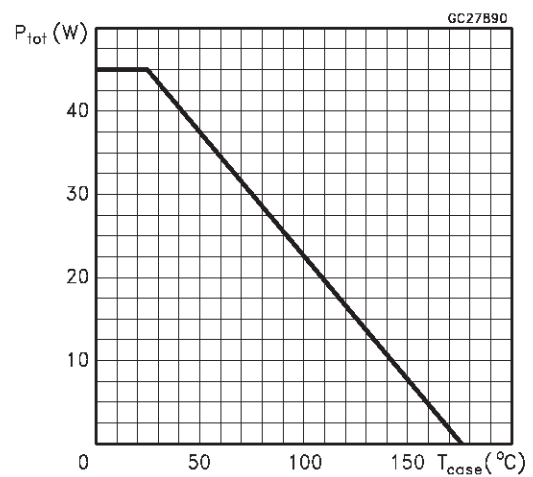
Thermal Impedance for ISOWATT220



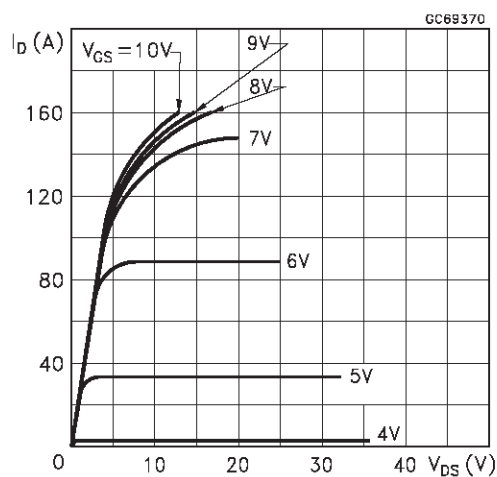
Derating Curve for TO-220



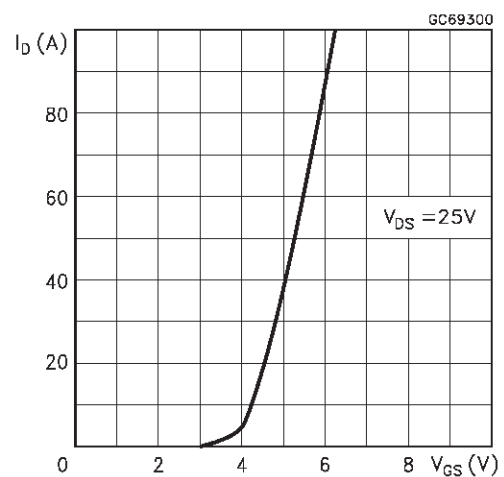
Derating Curve for ISOWATT220



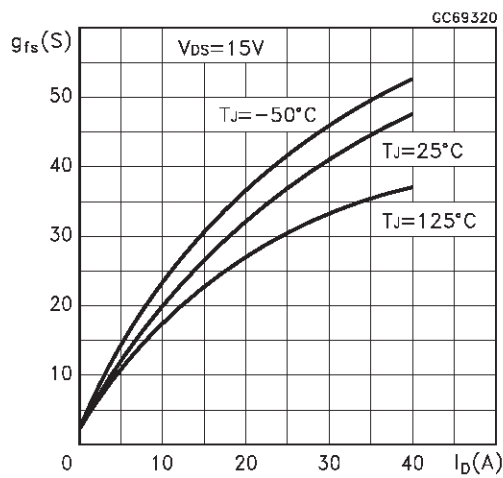
Output Characteristics



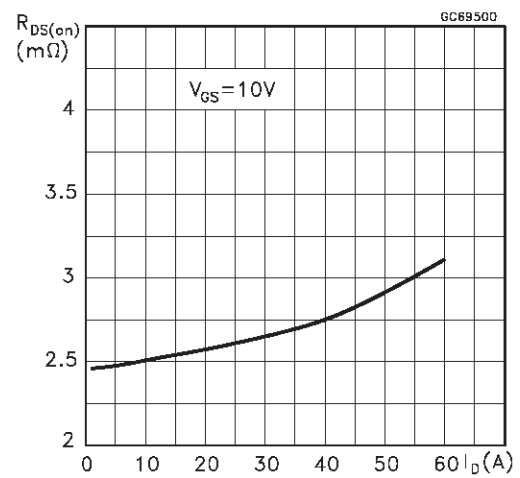
Transfer Characteristics



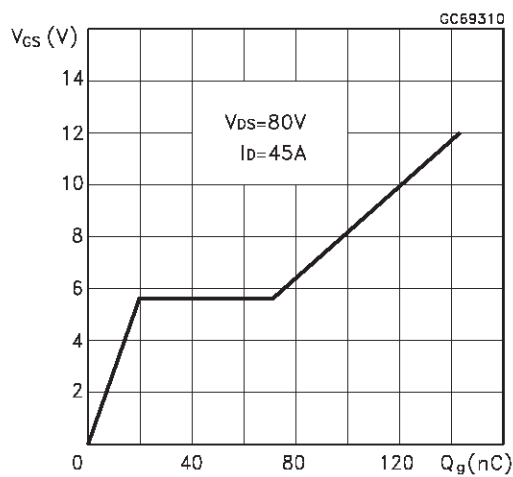
Transconductance



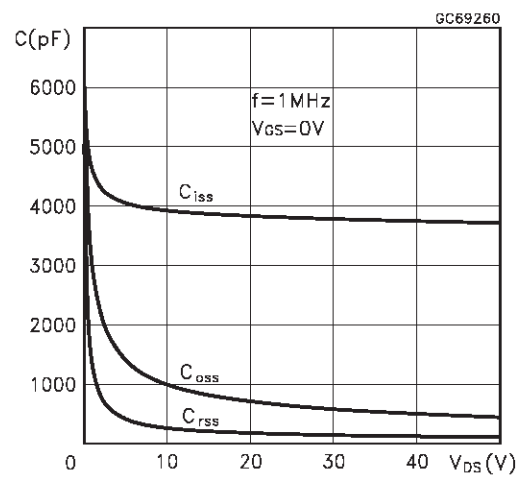
Static Drain-source On Resistance



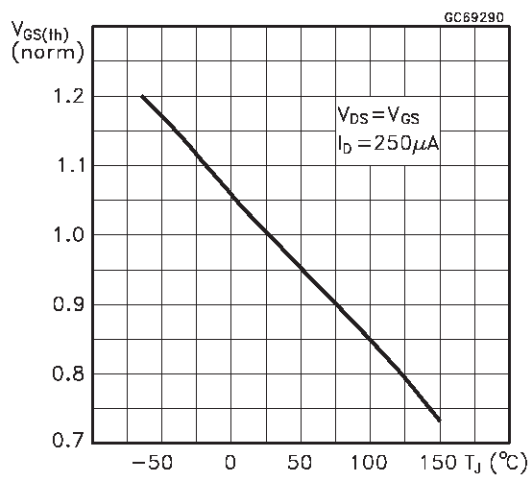
Gate Charge vs Gate-source Voltage



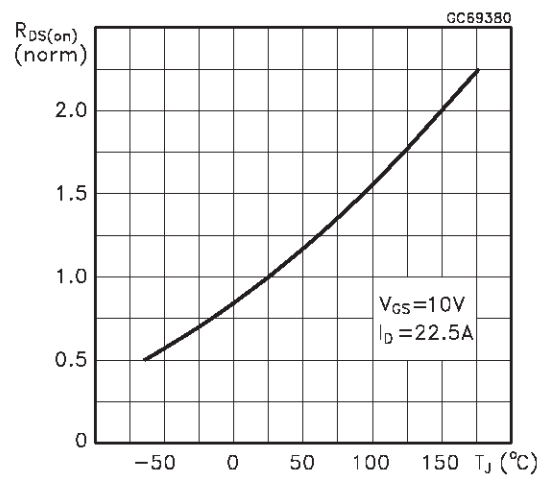
Capacitance Variations



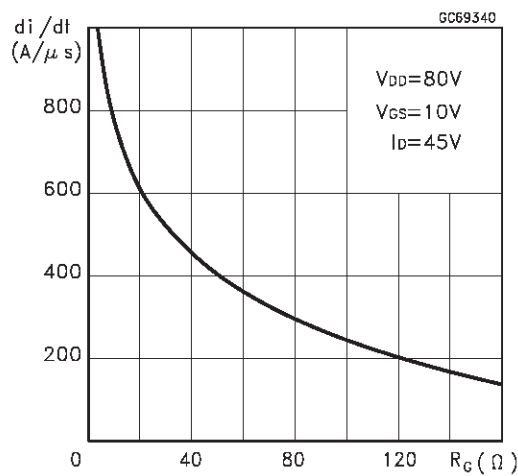
Normalized Gate Threshold Voltage vs Temperature



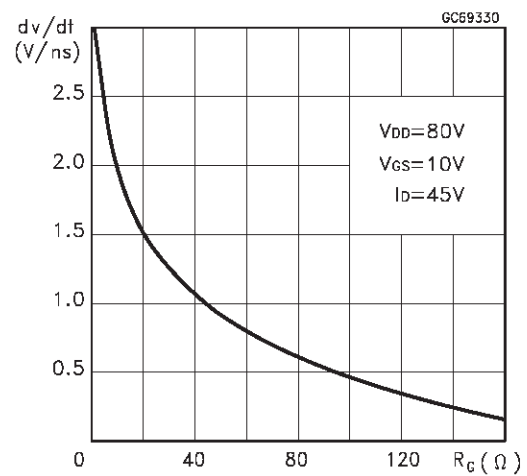
Normalized On Resistance vs Temperature



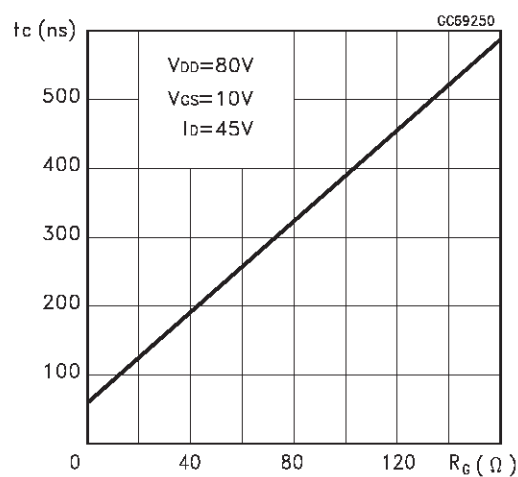
Turn-on Current Slope



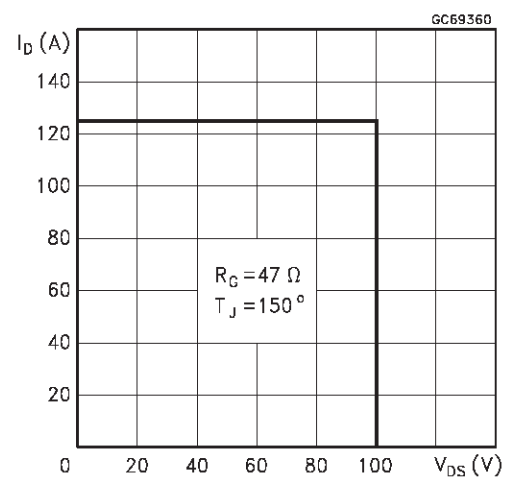
Turn-off Drain-source Voltage Slope



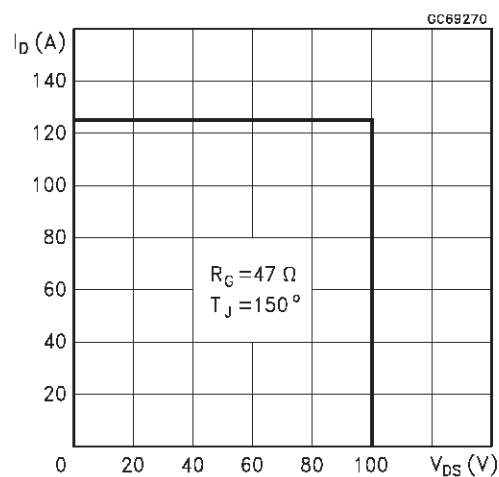
Cross-over Time



Switching Safe Operating Area



Accidental Overload Area



Source-drain Diode Forward Characteristics

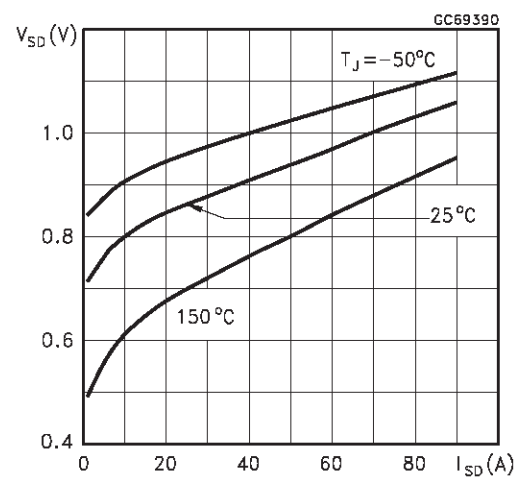
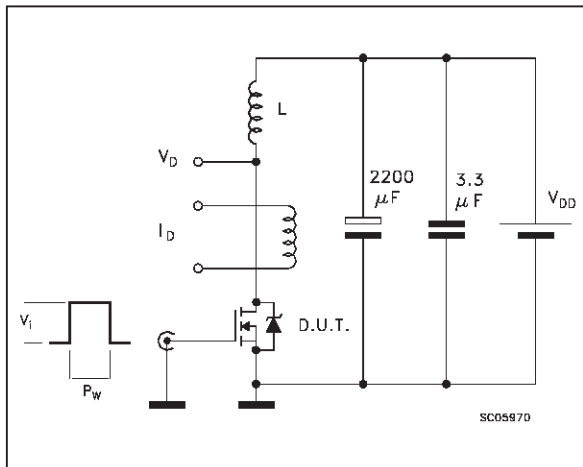
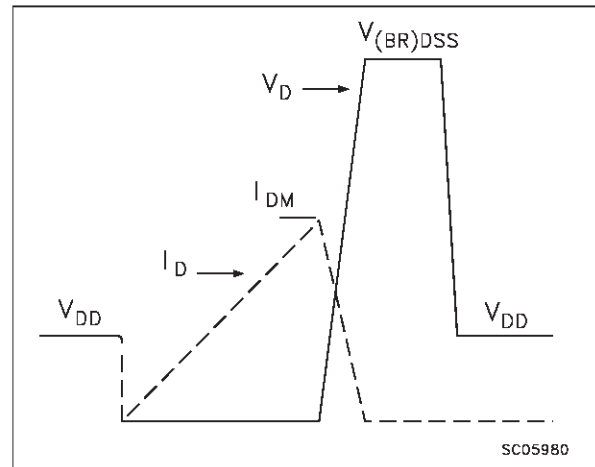
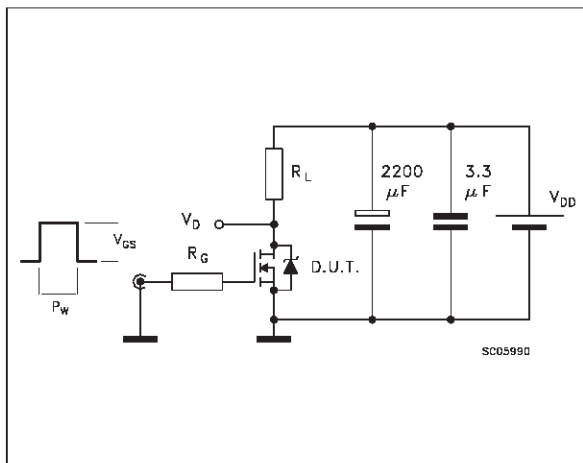
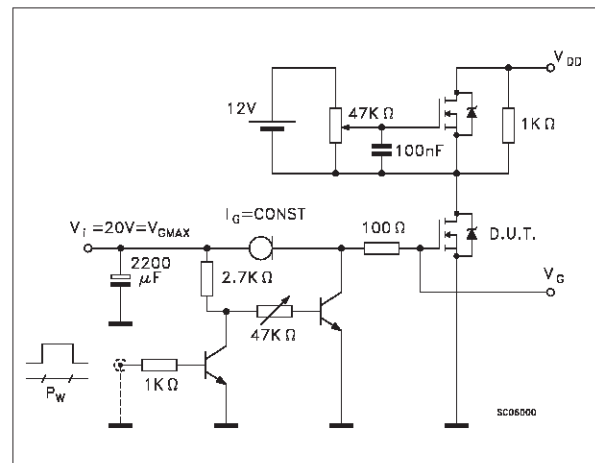
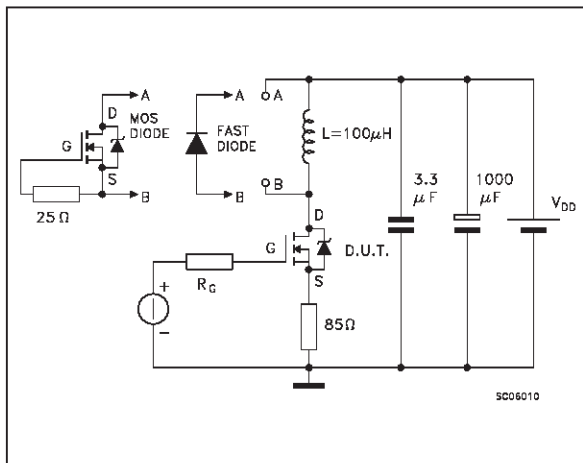
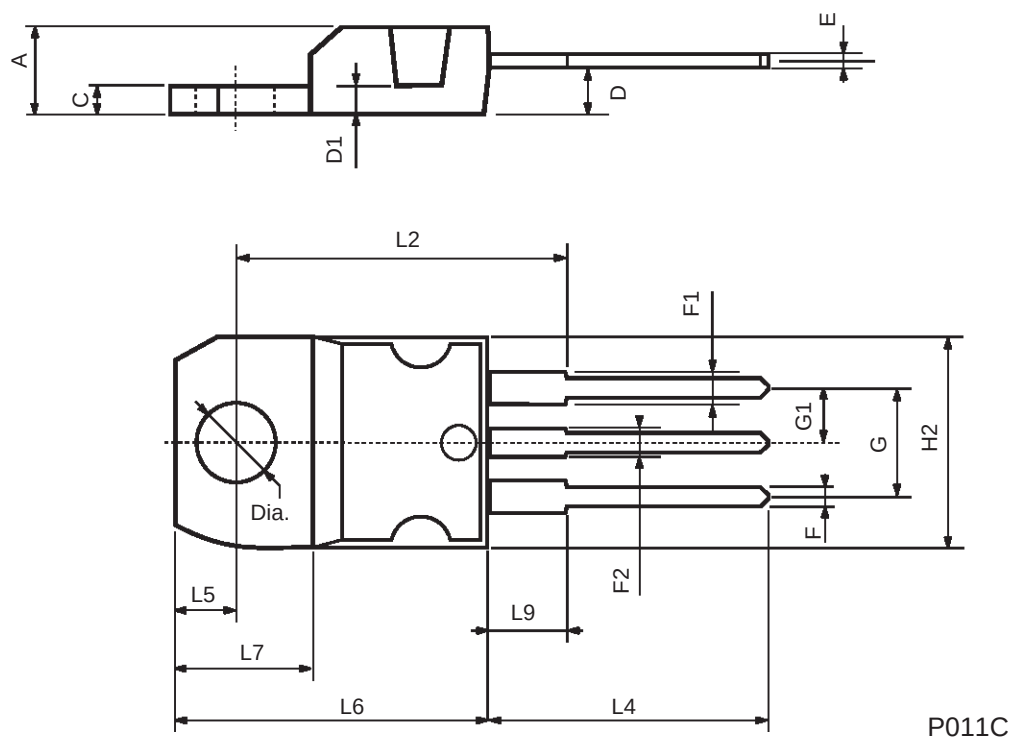


Fig. 1: Unclamped Inductive Load Test Circuit**Fig. 2: Unclamped Inductive Waveform****Fig. 3: Switching Times Test Circuits For Resistive Load****Fig. 4: Gate Charge test Circuit****Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**

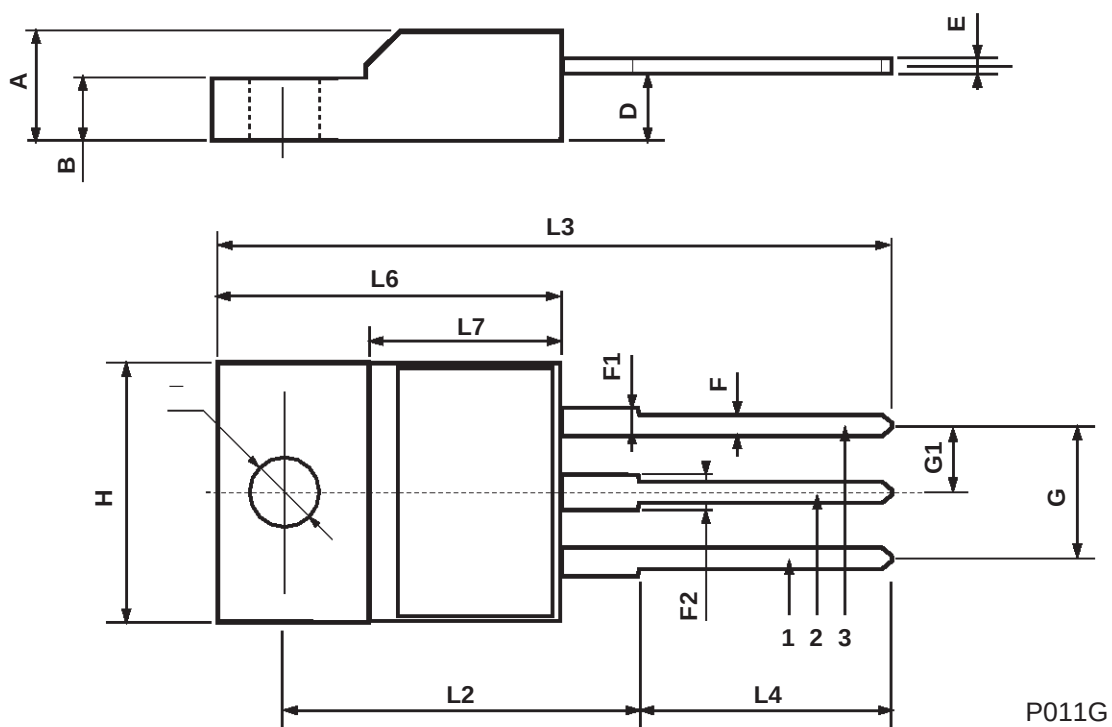
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



ISOWATT220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.4		0.7	0.015		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



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